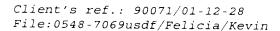
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- What Is Claimed Is: 1. A method for etching a mask layer, comprising steps of: 1
- forming a mask layer on a semiconductor substrate; 2
- forming a photoresist with patterns on the surface of the 3
- forming a victim layer on the surface of the photoresist mask layer; 5
- according to the photoresist topography, wherein the thickness 6
- of the victim layer is smaller than that of the photoresist, such
- that a plurality of slopes are formed on the sidewalls of the
- photoresist; and
- etching the mask layer using the photoresist and the victim 9 10
- layer with the slopes to be the etching mask. 11
 - 2. The method for etching a mask layer as claimed in claim
 - 1, wherein the mask layer is a nitride. 1 2
 - 3. The method for etching mask layer as claimed in claim 1
 - 1, wherein the thickness of the victim layer is $800 \sim 1000 \mbox{\normalfont\AA}$.
 - 4. A method for etching a protecting layer for metal contact 1
 - windows, comprising steps of: 2
 - providing a semiconductor with semiconductor elements or 3
 - inner leads on the surface;

number in layer over the inner leads. ...+ na++na

 $\pm x_I \!\approx\! 1/i$



forming a victim layer on the surface of the photoresist according to the photoresist topography, wherein the thickness of the victim layer is smaller than that of the photoresist with patterns, such that a plurality of slopes are formed on the

12 sidewalls of the photoresist; and

etching the protecting layer to form a plurality of metal contacting windows using the photoresist and the victim layer with the slopes to be the etching mask.

- 5. The method for etching a protecting layer for metal contact windows as claimed in claim 4, wherein the protecting
- 3 layer is nitride.
- 1 6. The method for etching a protecting layer for metal
- 2 contact windows as claimed in claim 4, wherein the victim layer
- 3 is an anti-reflection coating layer.
- 7. The method for etching a protecting layer for metal contact windows as claimed in claim 4, wherein the thickness of the victim layer is 800~1000Å.
- 1 8. The method for etching a protecting layer for metal 2 contact windows as claimed in claim 4, wherein the plurality of 3 metal contacting windows are pad regions and fuse regions 1